

TK6A60W,S4VX Information



For Reference Only

Part Number TK6A60W,S4VX

Manufacturer Toshiba Semiconductor and Storage
Category Discrete Semiconductor Products
Transistors - FETs, MOSFETs - Single

Description MOSFETS N. CH. 600M 624 TO 2008M

Description MOSFET N CH 600V 6.2A TO-220SIS

Package TO-220-3 Full Pack, Isolated Tab

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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Certified Quality

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TK6A60W,S4VX Specifications

Manufacturer Part Number TK6A60W,S4VX Manufacturer Toshiba Semiconductor and Storage Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-220-3 Full Pack, Isolated Tab Series DTMOSIV FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 600V Current - Continuous Drain (Id) @ 25°C 6.2A (Ta) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 3.7V @ 310μA Gate Charge (Qg) (Max) @ Vgs 12nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 390pF @ 300V Vgs (Max) ±30V FET Feature Super Junction Power Dissipation (Max) 30W (Tc) Rds On (Max) @ Id, Vgs 750 mOhm @ 3.1A, 10V Operating Temperature 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220SIS Package / Case TO-220-3 Full Pack, Isolated Tab		
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PackageTO-220-3 Full Pack, Isolated TabSeriesDTMOSIVFET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)600VCurrent - Continuous Drain (Id) @ 25°C6.2A (Ta)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id3.7V @ 310µAGate Charge (Qg) (Max) @ Vgs12nC @ 10VInput Capacitance (Ciss) (Max) @ Vds390pF @ 300VVgs (Max)±30VFET FeatureSuper JunctionPower Dissipation (Max)30W (Tc)Rds On (Max) @ Id, Vgs750 mOhm @ 3.1A, 10VOperating Temperature150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220SISPackage / CaseTO-220SI Full Pack, Isolated Tab	Category	Discrete Semiconductor Products
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FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 600V Current - Continuous Drain (Id) @ 25°C 6.2A (Ta) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 3.7V @ 310µA Gate Charge (Qg) (Max) @ Vgs 12nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 390pF @ 300V Vgs (Max) ±30V FET Feature Super Junction Power Dissipation (Max) 30W (Tc) Rds On (Max) @ Id, Vgs 750 mOhm @ 3.1A, 10V Operating Temperature 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220SIS Package / Case To-220SIS	Package	TO-220-3 Full Pack, Isolated Tab
Technology Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 6.2A (Ta) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Super Junction Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Supeline Device Package Package / Case MOSFET (Metal Oxide) 600V 600V 600V 600V 62A (Ta) 10V 3.7V @ 310µA 3.7V @ 310µA 3.7V @ 310µA 390F @ 300V 430V 500V 500V	Series	DTMOSIV
Drain to Source Voltage (Vdss)600 VCurrent - Continuous Drain (Id) @ 25°C6.2A (Ta)Drive Voltage (Max Rds On, Min Rds On)10 VVgs(th) (Max) @ Id3.7 V @ 310μAGate Charge (Qg) (Max) @ Vgs12nC @ 10 VInput Capacitance (Ciss) (Max) @ Vds390pF @ 300 VVgs (Max)±30 VFET FeatureSuper JunctionPower Dissipation (Max)30W (Tc)Rds On (Max) @ Id, Vgs750 mOhm @ 3.1A, 10 VOperating Temperature150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220SISPackage / CaseTO-220-3 Full Pack, Isolated Tab	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 3.7V @ 310μA Gate Charge (Qg) (Max) @ Vgs 12nC @ 10V Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ±30V FET Feature Super Junction Power Dissipation (Max) Rds On (Max) @ Id, Vgs 750 mOhm @ 3.1A, 10V Operating Temperature 150°C (TJ) Mounting Type Through Hole Supplier Device Package Package / Case TO-220SIS Package / Case	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id3.7V @ 310μAGate Charge (Qg) (Max) @ Vgs12nC @ 10VInput Capacitance (Ciss) (Max) @ Vds390pF @ 300VVgs (Max)±30VFET FeatureSuper JunctionPower Dissipation (Max)30W (Tc)Rds On (Max) @ Id, Vgs750 mOhm @ 3.1A, 10VOperating Temperature150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220SISPackage / CaseTO-220-3 Full Pack, Isolated Tab	Drain to Source Voltage (Vdss)	600V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Super Junction Power Dissipation (Max) Again Temperature Super Junction 30W (Tc) Rds On (Max) @ Id, Vgs 750 mOhm @ 3.1A, 10V Operating Temperature 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220SIS Package / Case TO-220-3 Full Pack, Isolated Tab	Current - Continuous Drain (Id) @ 25°C	6.2A (Ta)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ET Feature Super Junction Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Super Junction 750 mOhm @ 3.1A, 10V Operating Temperature 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220SIS Package / Case TO-220-3 Full Pack, Isolated Tab	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ET Feature Super Junction Power Dissipation (Max) Rds On (Max) @ Id, Vgs 750 mOhm @ 3.1A, 10V Operating Temperature 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220SIS Package / Case TO-220-3 Full Pack, Isolated Tab	Vgs(th) (Max) @ Id	3.7V @ 310μA
Vgs (Max)±30VFET FeatureSuper JunctionPower Dissipation (Max)30W (Tc)Rds On (Max) @ Id, Vgs750 mOhm @ 3.1A, 10VOperating Temperature150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220SISPackage / CaseTO-220-3 Full Pack, Isolated Tab	Gate Charge (Qg) (Max) @ Vgs	12nC @ 10V
FET Feature Super Junction Power Dissipation (Max) 30W (Tc) Rds On (Max) @ Id, Vgs 750 mOhm @ 3.1A, 10V Operating Temperature 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220SIS Package / Case TO-220-3 Full Pack, Isolated Tab	Input Capacitance (Ciss) (Max) @ Vds	390pF @ 300V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 750 mOhm @ 3.1A, 10V Operating Temperature 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220SIS Package / Case TO-220-3 Full Pack, Isolated Tab	Vgs (Max)	±30V
Rds On (Max) @ Id, Vgs750 mOhm @ 3.1A, 10VOperating Temperature150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220SISPackage / CaseTO-220-3 Full Pack, Isolated Tab	FET Feature	Super Junction
Operating Temperature 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220SIS Package / Case TO-220-3 Full Pack, Isolated Tab	Power Dissipation (Max)	30W (Tc)
Mounting Type Through Hole Supplier Device Package TO-220SIS Package / Case TO-220-3 Full Pack, Isolated Tab	Rds On (Max) @ Id, Vgs	750 mOhm @ 3.1A, 10V
Supplier Device Package TO-220SIS Package / Case TO-220-3 Full Pack, Isolated Tab	Operating Temperature	150°C (TJ)
Package / Case TO-220-3 Full Pack, Isolated Tab	Mounting Type	Through Hole
	Supplier Device Package	TO-220SIS
Report errors?	Package / Case	TO-220-3 Full Pack, Isolated Tab
		Report errors?

TK6A60W,S4VX Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

TK6A60W,S4VX Payment Methods



















TK6A60W,S4VX Shipping Methods













If you have any question about TK6A60W,S4VX, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com